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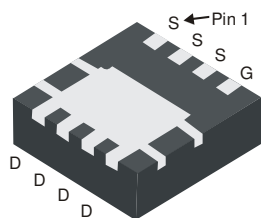
**60V N-CHANNEL ENHANCEMENT MODE MOSFET
POWERDI**
Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_C = +25^\circ C$
60V	50m Ω @ $V_{GS} = 10V$	18A
	63m Ω @ $V_{GS} = 4.5V$	16A

Description and Applications

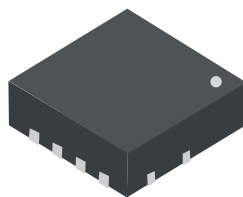
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

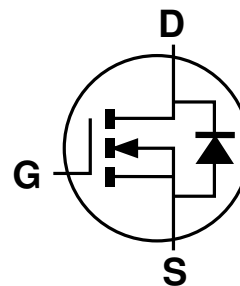


Bottom View

PowerDI3333-8



Top View



Equivalent Circuit

Features and Benefits

- Low $R_{DS(ON)}$ – Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products (PowerDI®)
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

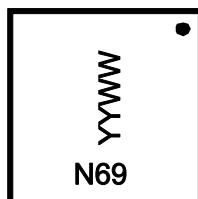
Mechanical Data

- Case: PowerDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.03 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN6069SFG-7	PowerDI3333-8	2,000/Tape & Reel
DMN6069SFG-13	PowerDI3333-8	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information


N69 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 16 = 2016)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	5.6 4.5	A
	Steady State	T _C = +25°C T _C = +70°C	I _D	18 14.5	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I _{DM}	25	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	2.5	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	12	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	7.2	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P _D	0.93	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	134	°C/W
	t < 10s		82	
Total Power Dissipation (Note 6)		P _D	2.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	53	°C/W
	t < 10s		33	
Thermal Resistance, Junction to Case		R _{θJC}	5	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	µA	V _{DS} = 60V, V _{GS} = 0V
Zero Gate Voltage Drain Current T _J = +150°C (Note 9)	I _{DSS}	—	—	100	µA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	39	50	mΩ	V _{GS} = 10V, I _D = 4.5A
		—	47	63		V _{GS} = 4.5V, I _D = 3A
Diode Forward Voltage	V _{SD}	—	—	1.1	V	V _{GS} = 0V, I _S = 2.5A
On State Drain Current (Note 9)	I _{D(ON)}	20	—	—	A	V _{DS} ≥ 5V, V _{GS} = 10V
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	740	1,480	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	40	80	pF	
Reverse Transfer Capacitance	C _{RSS}	—	28	55	pF	
Gate Resistance	R _G	—	2.2	4	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	6.4	12	nC	V _{DS} = 30V, I _D = 12A
Total Gate Charge (V _{GS} = 10V)	Q _G	—	14	25	nC	
Gate-Source Charge	Q _{GS}	—	2.8	5.5	nC	
Gate-Drain Charge	Q _{GD}	—	2.3	5	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.6	10	ns	V _{DS} = 30V, I _D = 12A V _{GS} = 10V, R _G = 6.0Ω
Turn-On Rise Time	t _R	—	5.0	10	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	12	24	ns	
Turn-Off Fall Time	t _F	—	3.3	10	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	11	22	ns	I _F = 4.5A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	5.1	10	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

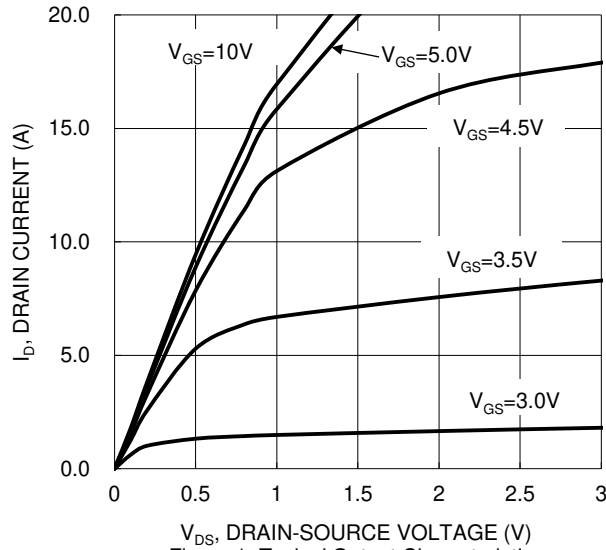


Figure 1. Typical Output Characteristic

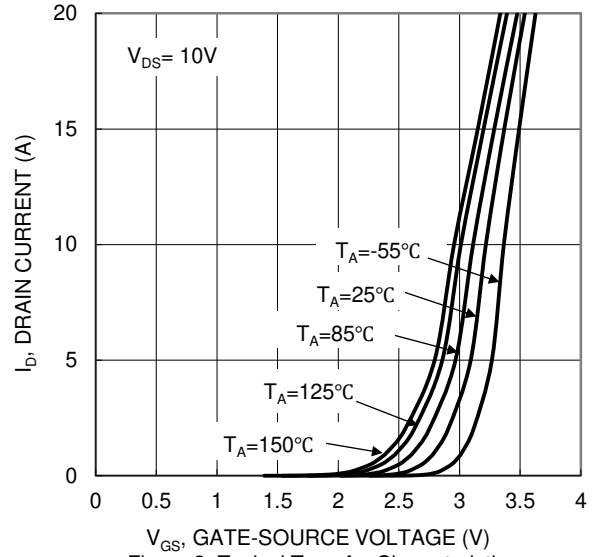


Figure 2. Typical Transfer Characteristic

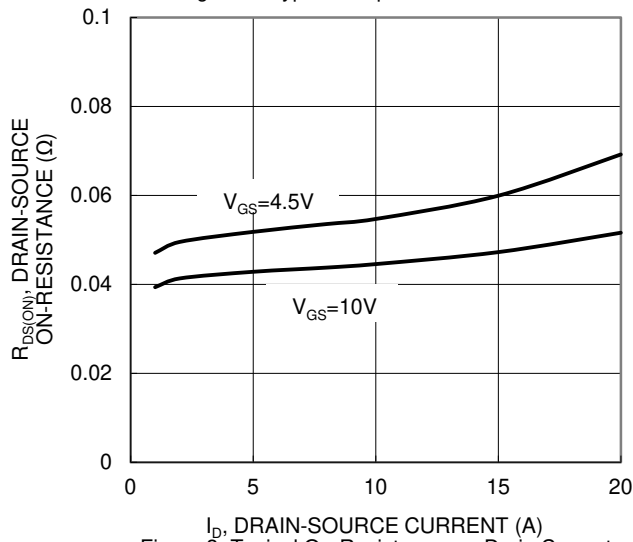


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

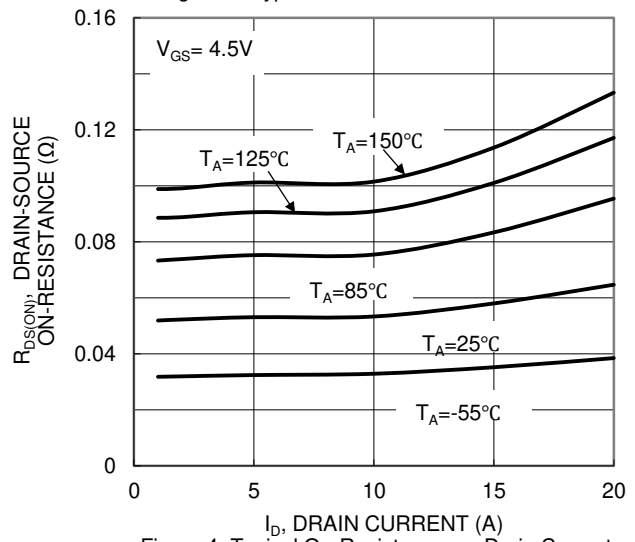


Figure 4. Typical On-Resistance vs. Drain Current and Temperature

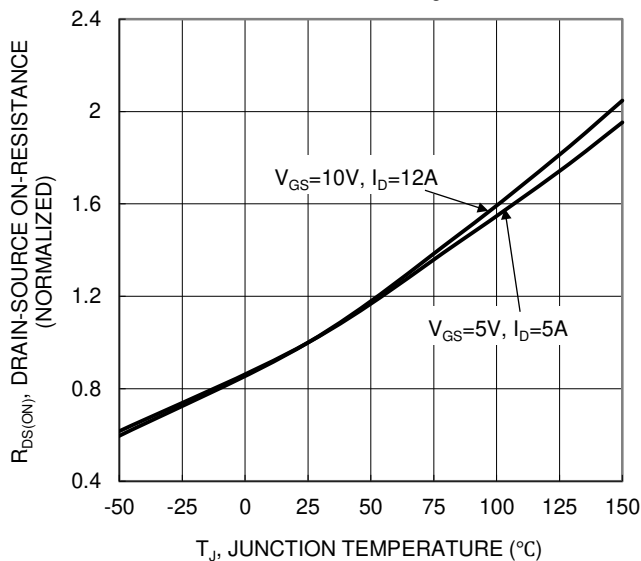


Figure 5. On-Resistance Variation with Temperature

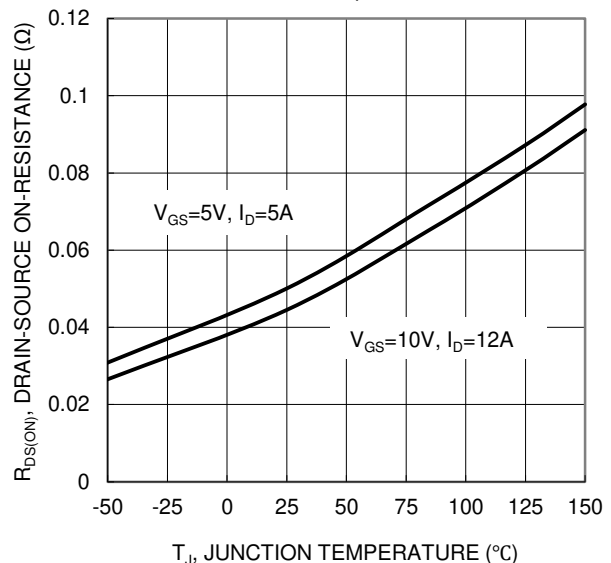
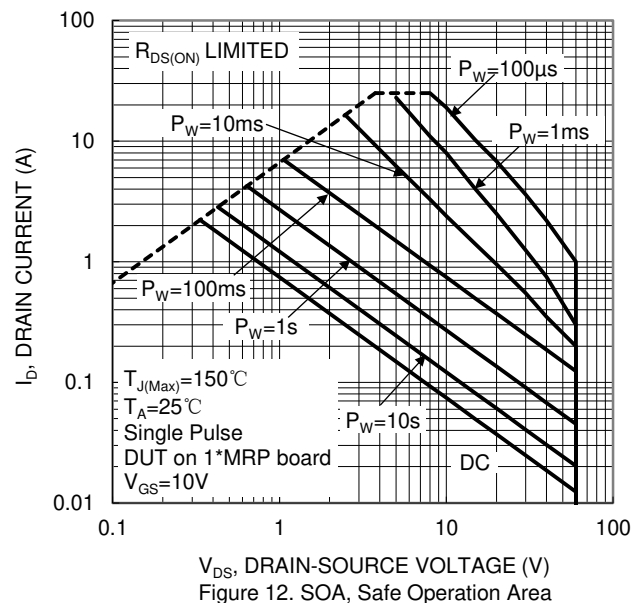
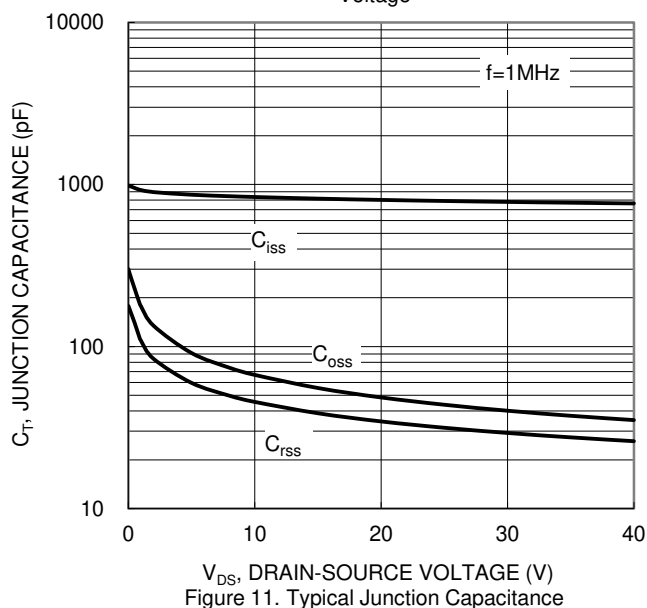
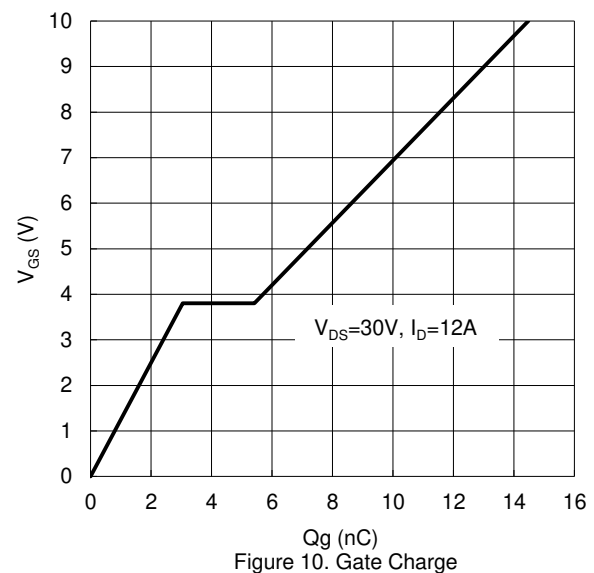
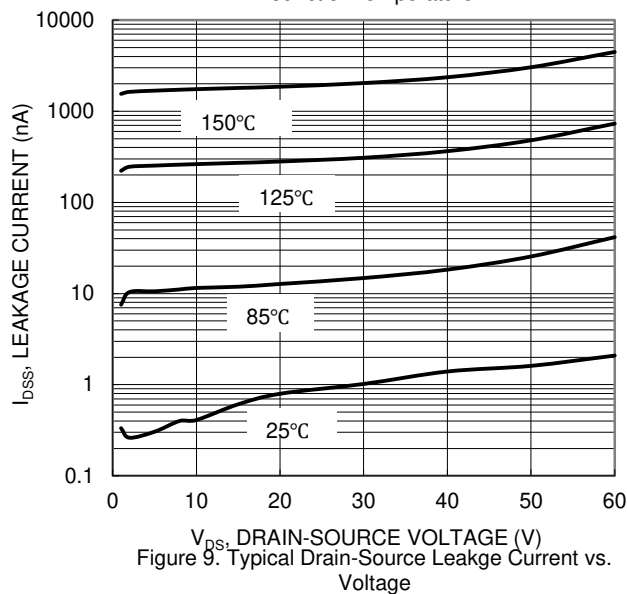
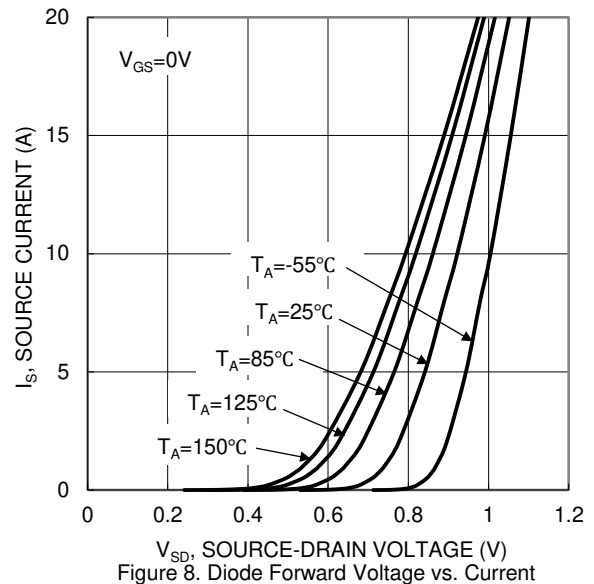
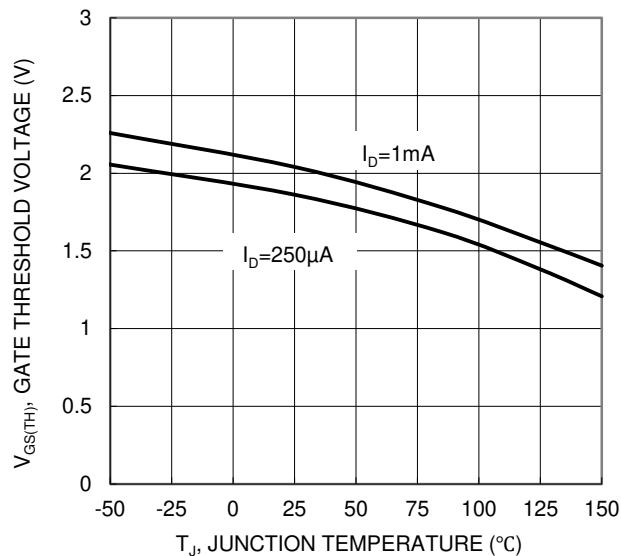


Figure 6. On-Resistance Variation with Temperature



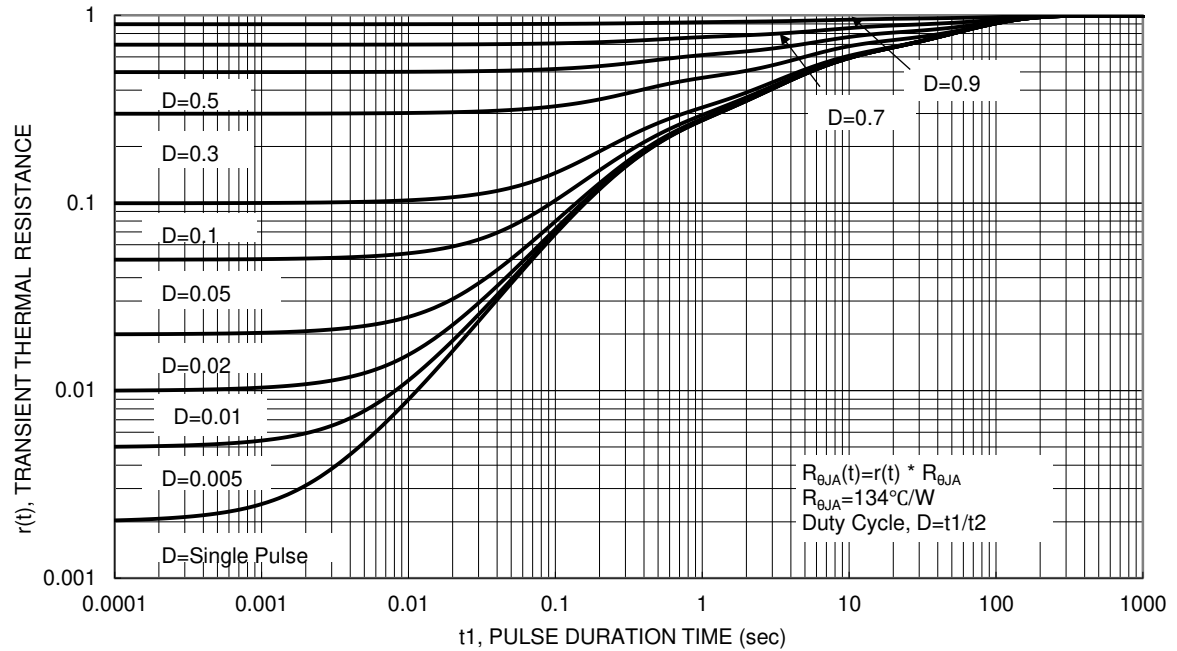
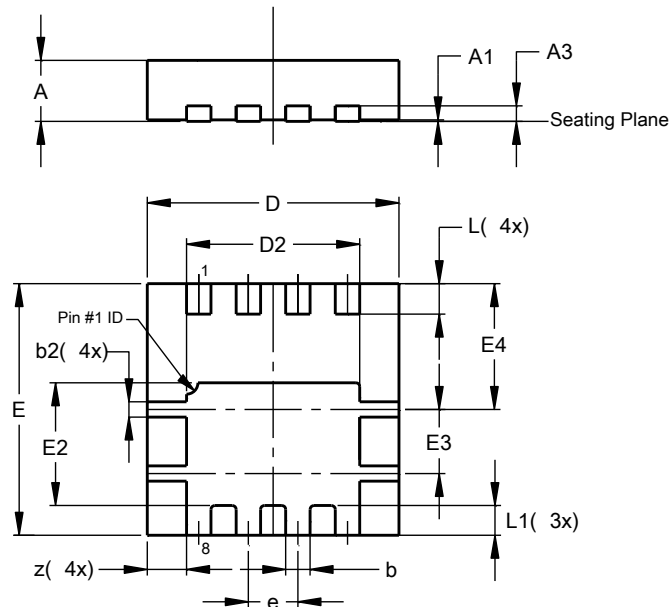


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8

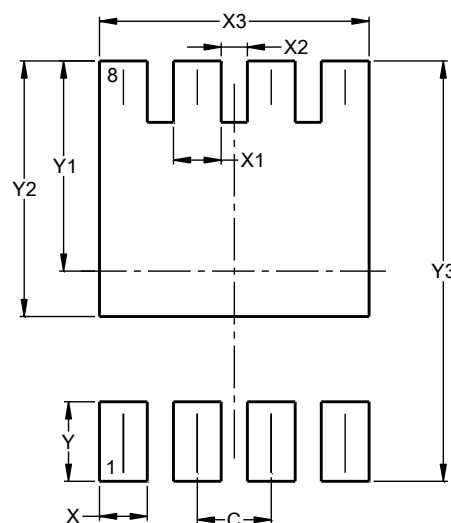


PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	—	—	0.65
L	0.35	0.45	0.40
L1	—	—	0.39
z	—	—	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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